



DR. MINN-TSONG LIN

National Taiwan University

PERPENDICULAR MAGNETIC ANISOTROPY DRIVEN BY FERROMAGNETIC/ ANTIFERROMAGNETIC EXCHANGE COUPLING

A novel perpendicular anisotropy and new kind of spin-reorientation transition were found in ferromagnetic/antiferromagnetic bilayer system. The perpendicular anisotropy was found to be driven by an antiferromagnetic layer with suitable control of the thickness. This bilayer system can be used as a new building block for designing nanomagnetic device or storage media with perpendicular magnetization.

In details, Fe/Mn bilayers grown on $\text{Cu}_3\text{Au}(100)$ [1,2] were investigated. With increasing Mn thickness, the magnetic easy axis of 6 ML Fe/n ML Mn was observed to switch from in-plane to perpendicular direction by magneto-optical kerr effect (MOKE) and photo emission electron microscopy (PEEM) in application of synchrotron radiation. The PEEM provides the technique for element-specific magnetic domain imaging with help of magnetic circular dichroism effect and by selecting various absorption edges of different elements. The magnetic domain of antiferromagnetic Mn layer was shown to be antiparallel to the Fe domain in both regions of perpendicular and in-plane magnetization. The perpendicular magnetization is accompanied with the enhanced coercivity, being proposed to be attributed to the exchange coupling from Fe/Mn interface, which overcomes the in-plane anisotropy of the magnetic thin films. A detailed phase diagram at variation of thickness and temperature is given for optimizing material parameters and estimation of the effective perpendicular anisotropy as well.

[1] W. C. Lin, T. Y. Chen, L. C. Lin, B. Y. Wang, Y. W. Liao, K.-J. Song, and Minn-Tsong Lin, *Phys. Rev. B* **75**, 054419 (2007)

[2] W. C. Lin, B. Y. Wang, T. Y. Chen, L. C. Lin, Y. W. Liao, W. Pan, N. Y. Jih, and K. J. Song, and Minn-Tsong Lin, *Appl. Phys. Lett.* **90**, 052502 (2007).

Host:
**Sy-Hwang Liou &
Axel Enders**

**Wednesday, 24 June 2009
201 Brace Lab
1:30 p.m.**